

Amendments to the Claims:

Claims 1-54 (Canceled).

55. (Previously Presented): A semiconductor processing method comprising:

providing a semiconductor substrate comprising a first hydrophobic material, a second hydrophilic material received outwardly of the first hydrophobic material, and a third hydrophobic material received outwardly of the second hydrophilic material;

forming an opening through the third and second materials to the first material; and

exposing the first, second and third materials to a solution comprising ozone, water and a surfactant effective to form an oxide layer on the first hydrophobic material within the opening.

56. (Previously Presented): The method of claim 55 wherein the exposing is effective to form the oxide layer to be self-limiting in thickness to be less than or equal to 1 nanometer thick.

57. (Previously Presented): The method of claim 55 wherein the surfactant comprises a non-ionic material.

58. (Previously Presented): The method of claim 55 wherein the surfactant comprises a quaternary ammonium chloride material.

59. (Previously Presented): The method of claim 55 wherein the surfactant comprises a nonionic material selected from the group consisting of an ethoxylated sorbitan monooleate, and functional equivalents of ethoxylated sorbitan monooleate.

60. (Previously Presented): The method of claim 55 wherein the exposing comprises spraying the substrate with the solution within a chamber, the spraying comprising maintaining the solution at a first temperature between approximately 20° C and approximately 95° C, and the chamber at a second temperature between approximately 20° C and approximately 95° C.

61. (Previously Presented): The method of claim 60 wherein the first temperature and second temperature are approximately equal.

62. (Previously Presented): The method of claim 60 wherein the first temperature is higher than the second temperature.

63. (Previously Presented): The method of claim 60 wherein the first temperature is maintained between approximately 65° C and approximately 95° C.

64. (Previously Presented): The method of claim 55 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber.

65. (Previously Presented): The method of claim 55 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber which is greater than concentration of ozone in the solution.

66. (Previously Presented): The method of claim 55 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber, the gaseous atmosphere having a pressure in excess of atmospheric pressure.

67. (Previously Presented): The method of claim 55 wherein the water is deionized water.

68. (Previously Presented): The method of claim 55 wherein the first hydrophobic material comprises silicon.

69. (Previously Presented): The method of claim 55 wherein the second hydrophilic material comprises silicon oxide.

70. (Previously Presented): The method of claim 55 wherein the third hydrophobic material comprises silicon.

71. (Previously Presented): The method of claim 70 wherein the third hydrophobic material comprises polysilicon.

72. (Currently Amended): A semiconductor processing method comprising:

providing a semiconductor substrate comprising a silicon-containing silicon-containing region, a silicon oxide-containing oxide-containing layer received outwardly of the silicon-containing silicon-containing region, and a polysilicon-containing polysilicon-containing layer received outwardly of the silicon oxide-containing oxide-containing layer;

forming an opening through the polysilicon-containing polysilicon-containing layer and the silicon oxide-containing oxide-containing layer to the silicon-containing silicon-containing region; and

exposing the polysilicon-containing polysilicon-containing layer, the silicon oxide-containing oxide-containing layer and the silicon-containing silicon-containing region to a solution comprising ozone, water and a surfactant effective to form a silicon oxide comprising oxide-comprising layer on the silicon-containing silicon-containing region within the opening.

73. (Currently Amended): The method of claim 72 wherein the exposing is effective to form the oxide silicon oxide-containing layer to be self-limiting in thickness to be less than or equal to 1 nanometer thick.

74. (Previously Presented): The method of claim 72 wherein the surfactant comprises a non-ionic material.

75. (Previously Presented): The method of claim 72 wherein the surfactant comprises a quaternary ammonium chloride material.

76. (Previously Presented): The method of claim 72 wherein the surfactant comprises a nonionic material selected from the group consisting of an ethoxylated sorbitan monooleate, and functional equivalents of ethoxylated sorbitan monooleate.

77. (Previously Presented): The method of claim 72 wherein the exposing comprises spraying the substrate with the solution within a chamber, the spraying comprising maintaining the solution at a first temperature between approximately 20° C and approximately 95° C, and the chamber at a second temperature between approximately 20° C and approximately 95° C.

78. (Previously Presented): The method of claim 77 wherein the first temperature and second temperature are approximately equal.

79. (Previously Presented): The method of claim 77 wherein the first temperature is higher than the second temperature.

80. (Previously Presented): The method of claim 77 wherein the first temperature is maintained between approximately 65° C and approximately 95° C.

81. (Previously Presented): The method of claim 72 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber.

82. (Previously Presented): The method of claim 72 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber which is greater than concentration of ozone in the solution.

83. (Previously Presented): The method of claim 72 further comprising providing a gaseous atmosphere comprising a concentration of ozone within the process chamber, the gaseous atmosphere having a pressure in excess of atmospheric pressure.

84. (Previously Presented): The method of claim 72 wherein the water is deionized water.